TOSHIBA Photocoupler GaAs IRed & Photo-Triac

TLP561J

Triac Driver
Programmable Controllers
AC-Output Module
Solid State Relay

The TOSHIBA TLP561J consists of a zero voltage crossing turn–on photo–triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

• Peak off-state voltage: 600V(min.)

• On-state current: 100mA(max.)

• Isolation voltage: 2500V_{rms}(min.)

• UL recognized: UL1577, file no. E67349

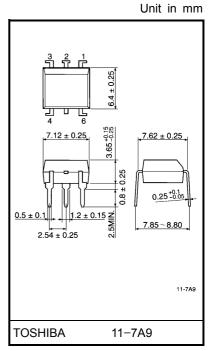
• Trigger LED current

Classi– Fication*	Trigger LED	Current (mA)	Marking Of		
	V _T =6V, Ta=25°C		Classification		
	Min.	Max.			
(IFT7)	ı	7	T7		
Standard	_	10	T7, blank		

*Ex. (IFT7); TLP561J(IFT7)

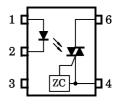
(Note): Application type name for certification test, please use standard product type name, i.e. TLP561J(IFT7): TLP561J

*1: According to VDE0110, table 4.



Weight: 0.39g

Pin Configuration (top view)



1 : ANODE 2 : CATHODE

3 : N.C.

4: TERMINAL 1 6: TERMINAL 2

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit		
	Forward current	I _F	50	mA		
LED	Forward current derating (Ta ≥	ΔI _F / °C	-0.7	mA / °C		
	Peak forward current (100µs pu	lse, 100pps)	I _{FP}	1	Α	
	Reverse voltage		V _R	5	V	
	Junction temperature	Tj	125	°C		
	Off-state output terminal voltag	V_{DRM}	600	V		
	On-state RMS current	Ta = 25°C	I	100	mA	
_		Ta = 70°C	I _{T(RMS)}	50		
Detector	On–state current derating (Ta ≥	ΔI _T / °C	-1.1	mA / °C		
	Peak on-state current (100µs p	I _{TP}	2	Α		
	Peak nonrepetitive surge currer (Pw = 10ms, DC = 10%)	I _{TSM}	1.2	А		
	Junction temperature	Tj	115	°C		
Storag	Storage temperature range			-55~125	°C	
Operating temperature range		T _{opr}	-40~100	°C		
Lead soldering temperature (10s)			T _{sol}	260	°C	
Isolation voltage (AC, 1min., R.H. ≤ 60%)			BVS	2500	V _{rms}	

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{AC}	_	_	240	V _{ac}
Forward current	l _F	15	20	25	mA
Peak on-state current	I _{TP}	_	_	_	Α
Operating temperature	T _{opr}	-25	_	85	°C

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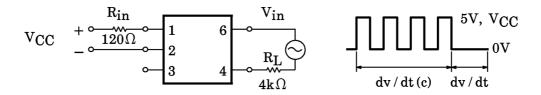
Individual Electrical Characteristics (Ta = 25°C)

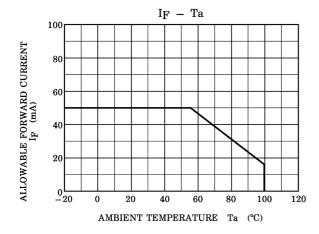
Characteristic		Symbol	Test Condition		Min.	Тур.	Max.	Unit
LED	Forward voltage	V _F	I _F = 10mA		1.0	1.15	1.3	V
	Reverse current	I _R	V _R = 5 V		_	_	10	μA
	Capacitance	C _T	V = 0, f = 1MHz		_	30		pF
Detector	Peak off-state current	I _{DRM}	V _{DRM} = 600V		_	10	1000	nA
	Peak on-state voltage	V_{TM}	I _{TM} = 100mA		_	1.7	3.0	V
	Holding current	lΗ	_		_	0.6		mA
	Critical rate of rise of off–state voltage	dv / dt	V _{in} = 240V _{rms} , Ta = 85°C	(Fig.1)	200	500	ı	V / µs
	Critical rate of rise of commutating voltage	dv / dt(c)	$V_{in} = 60V_{rms}$, $I_T = 15mA$	(Fig.1)	_	0.2		V / µs

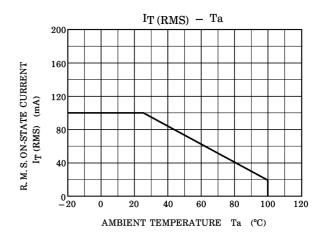
Coupled Electrical Characteristics (Ta = 25°C)

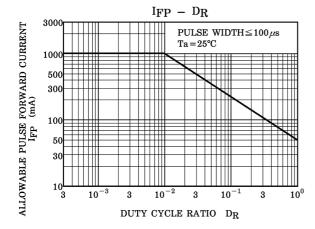
Characteristics	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Trigger LED current	I _{FT}	$V_T = 6V, R_L = 100\Omega$	_	5	10	mA
Inhibit voltage	V _{IH}	I _F = Rated I _{FT}	_	_	50	V
Leakage in inhibited state	lн	I _F = Rated I _{FT} V _T = Rated V _{DRM}	_	200	600	μΑ
Capacitance (input to output)	CS	V _S = 0, f = 1MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S = 500V	5×10 ¹⁰	10 ¹⁴	_	Ω
	BVS	AC, 1 minute	2500	_	_	V _{rms}
Isolation voltage		AC, 1 second, in oil	_	5000	_	
		DC, 1 minute, in oil	_	5000	_	V _{dc}

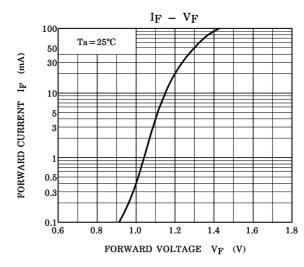
Fig.1: dv / dt test circuit

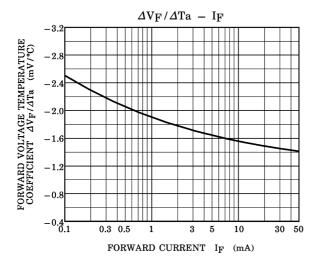


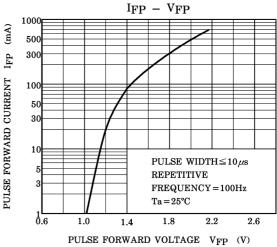




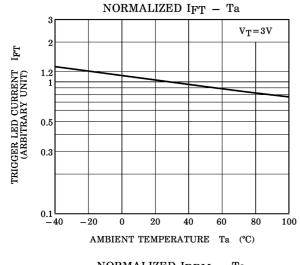


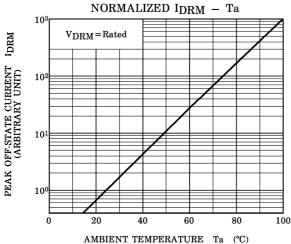


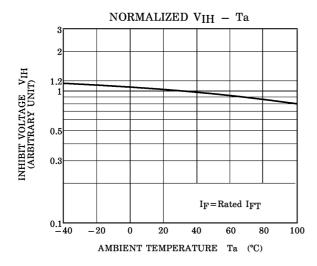


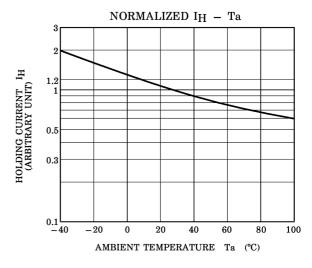


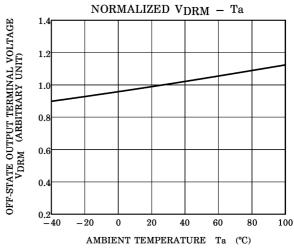
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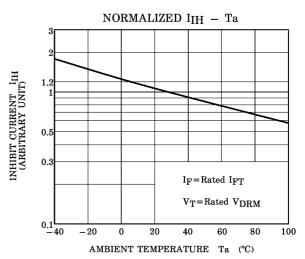












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